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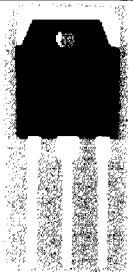
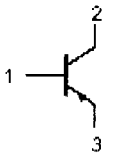
Silicon PNP Power Transistor

2SA1292

DESCRIPTION

- Low Collector Saturation Voltage-
  : $V_{CE(sat)}$= -0.4V(Max.)@I_C= -7.5A
- Fast Switching Speed
- Complement to Type 2SC3256





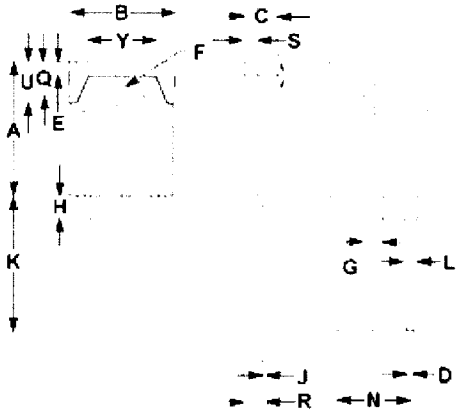
PIN: 1.Base
2.Collector
3.Emitter

1 2 3

TO-3PN Package

APPLICATIONS

- Various inductance lamp drivers for electrical equipment.
- Inverters,converters(strobo,flash,fluorescent lamp lighting circuits).
- Power amplifier (high power car stereo, motor controller).
- High-speed switching (switching regulator, driver).



DIM	mm MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-15	A
I_{CM}	Collector Current-Peak	-20	A
P_C	Collector Power Dissipation @ T_C=25℃	80	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -1mA; R_{BE}= ∞	-60			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -1mA; I_E= 0	-80			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -1mA; I_C= 0	-5			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -7.5A; I_B= -0.375A			-0.4	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -40V; I_E= 0			-100	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= -4V; I_C= 0			-100	μ A
h_{FE}	DC Current Gain	I_C= -1A; V_{CE}= -2V	70		280	
f_T	Current-Gain—Bandwidth Product	I_C= -1A; V_{CE}= -5V		100		MHz

Switching Times

t_{on}	Turn-on Time	I_C= -6A, R_L= 3.3Ω , I_{B1}= -I_{B2}= -0.3A, V_{CC}≈-20V		0.1		μ s
t_{stg}	Storage Time			0.5		μ s
t_f	Fall Time			0.1		μ s

◆ h_{FE} Classifications

Q	R	S
70-140	100-200	140-280